

Power Bridge Rectifiers

SKD 53

Features

- Glass passivated silicon chips
- Low thermal impedance through use of direct copper bonded aluminum substrate (DCB) base plate
- Blocking voltage up to 1800 V
- Suitable for PCB mounting and wave soldering
- For applications with high vibrations we recommend to fasten the bridge to the pcb with 4 selftapping screw

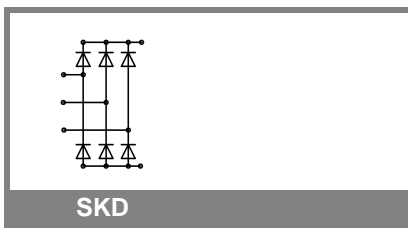
Typical Applications

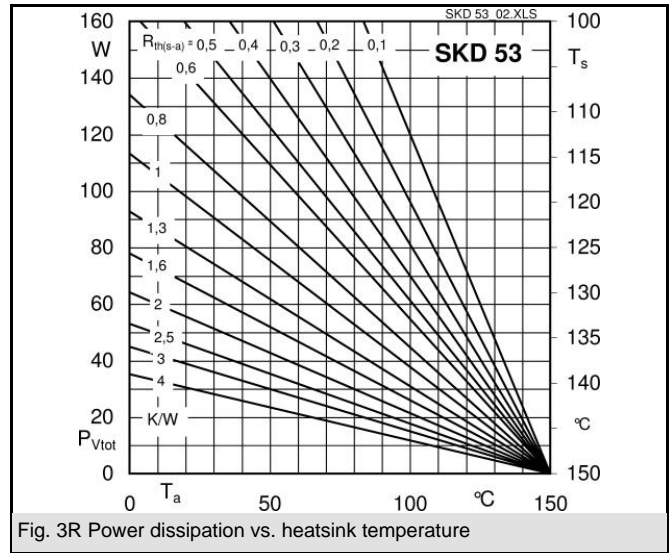
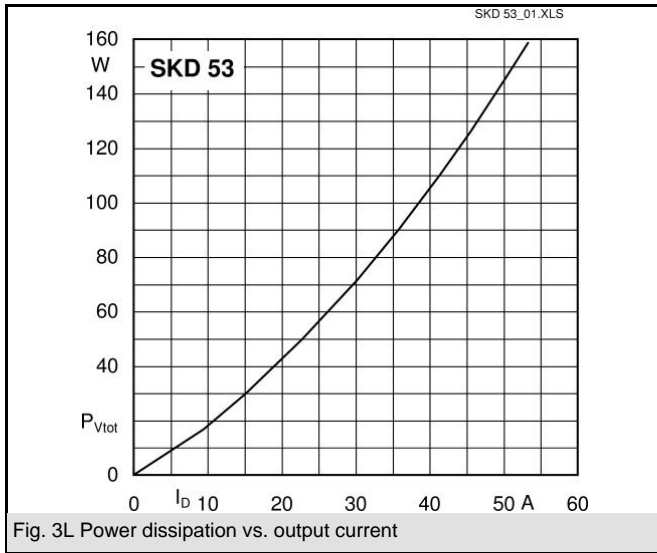
- Three phase rectifiers for power supplies
- Input rectifiers for variable frequency drives
- Rectifiers for DC motor field supplies
- Battery charger rectifiers

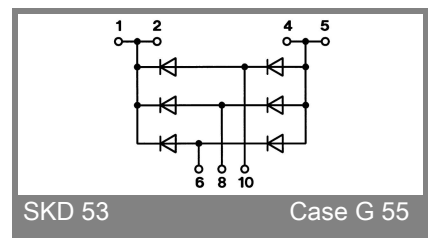
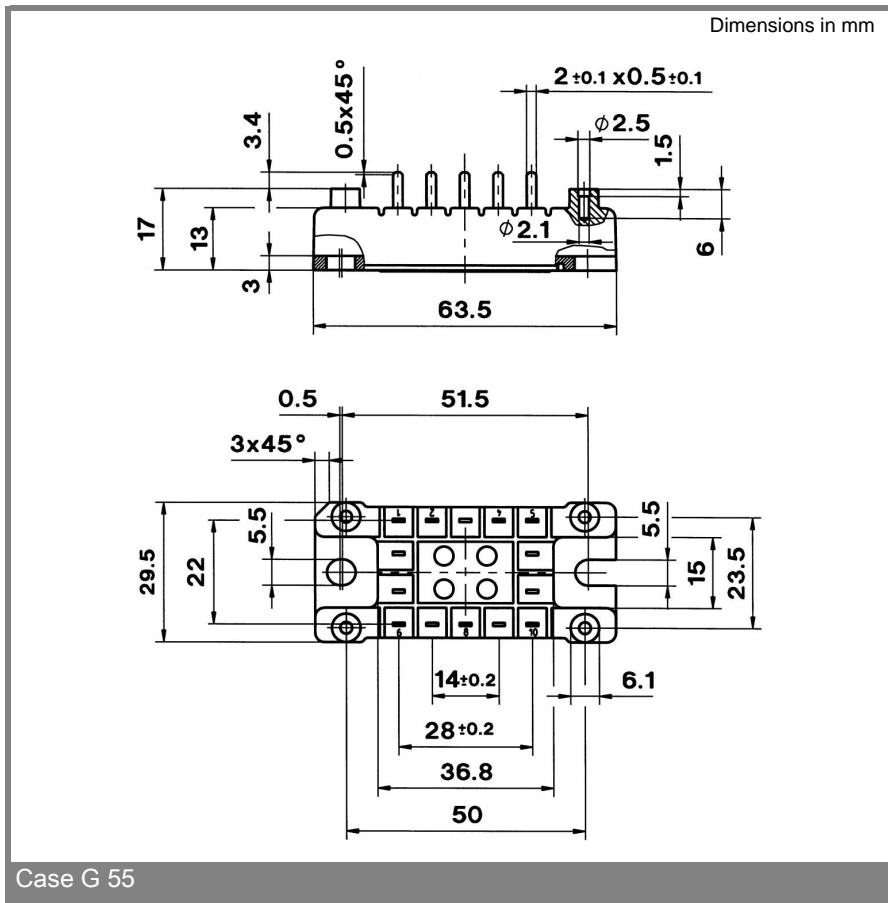
- 1) Freely suspended or mounted on an insulator
- 2) Mounted on a painted metal sheet of min. 250 x 250 x 1 mm
- 3) $T_{\text{solder}} = 250 \pm 10 \text{ }^\circ\text{C}$ (10 s)

V_{RSM} V	$V_{\text{RRM}}, V_{\text{DRM}}$ V	$I_{\text{D}} = 53 \text{ A}$ (full conduction) ($T_{\text{s}} = 100 \text{ }^\circ\text{C}$)
500	400	SKD 53/04
900	800	SKD 53/08
1300	1200	SKD 53/12
1600	1400	SKD 53/14
1700	1600	SKD 53/16
1900	1800	SKD 53/18

Symbol	Conditions	Values	Units
I_{D}	$T_{\text{s}} = 100 \text{ }^\circ\text{C}$	53	A
	$T_{\text{a}} = 45 \text{ }^\circ\text{C}$; isolated ¹⁾	4	A
	$T_{\text{a}} = 45 \text{ }^\circ\text{C}$; chassis ²⁾	18	A
	$T_{\text{a}} = 45 \text{ }^\circ\text{C}$; P5A/100 (R4A/120)	27 (29)	A
	$T_{\text{a}} = 35 \text{ }^\circ\text{C}$; P1A/120F	63	A
I_{FSM}	$T_{\text{vj}} = 25 \text{ }^\circ\text{C}$; 10 ms	370	A
	$T_{\text{vj}} = 150 \text{ }^\circ\text{C}$; 10 ms	270	A
i^2t	$T_{\text{vj}} = 25 \text{ }^\circ\text{C}$; 8,3 ... 10 ms	685	A ² s
	$T_{\text{vj}} = 150 \text{ }^\circ\text{C}$; 8,3 ... 10 ms	365	A ² s
V_{F}	$T_{\text{vj}} = 25 \text{ }^\circ\text{C}$; $I_{\text{F}} = 50 \text{ A}$	max. 1,5	V
$V_{\text{(TO)}}$	$T_{\text{vj}} = 150 \text{ }^\circ\text{C}$	max. 0,8	V
r_{T}	$T_{\text{vj}} = 150 \text{ }^\circ\text{C}$	max. 13	mΩ
I_{RD}	$T_{\text{vj}} = 25 \text{ }^\circ\text{C}$; $V_{\text{DD}} = V_{\text{DRM}}$; $V_{\text{RD}} = V_{\text{RRM}}$	max. 0,2	mA
	$T_{\text{vj}} = 150 \text{ }^\circ\text{C}$; $V_{\text{RD}} = V_{\text{RRM}}$	4	mA
$R_{\text{th(j-s)}}$	per diode	1,9	K/W
	total	0,317	K/W
$R_{\text{th(j-a)}}$	isolated ¹⁾	14,92	K/W
	chassis ²⁾	2,92	K/W
T_{vj}		- 40 ... + 150	°C
T_{stg}		- 40 ... + 125 ³⁾	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 (3000)	V
M_{s}	to heatsink; SI units	2 ± 15 %	Nm
M_{t}			
a		5 * 9,81	m/s ²
m		30	g
Case		G 55	







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